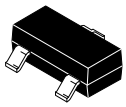
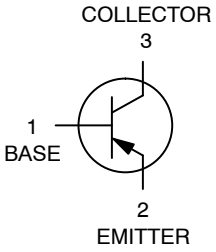
Driver Transistors

PNP Silicon

MMBTA55L Series, MMBTA56L Series, SMMBTA56L Series



SOT−23
CASE 318
STYLE 6



Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector − Emitter Voltage MMBTA55 MMBTA56, SMMBTA56	V_{CEO}	 −60 −80	Vdc
Collector − Base Voltage MMBTA55 MMBTA56, SMMBTA56	V_{CBO}	 −60 −80	Vdc
Emitter − Base Voltage	V_{EBO}	−4.0	Vdc
Collector Current − Continuous	I_C	−500	mAdc

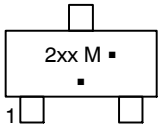
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR− 5 Board (Note 1) T_A = 25°C Derate above 25°C	P_D	 225 1.8	 mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T_A = 25°C Derate above 25°C	P_D	 300 2.4	 mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T_J, T_{stg}	−55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR− 5 = 1.0 × 0.75 × 0.062 in.
2. Alumina = 0.4 × 0.3 × 0.024 in. 99.5% alumina.

MARKING DIAGRAM



2xx = Device Code
x = H for MMBTA55LT1G
xx = GM for MMBTA56LT1G, SMMBTA56LT1G
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

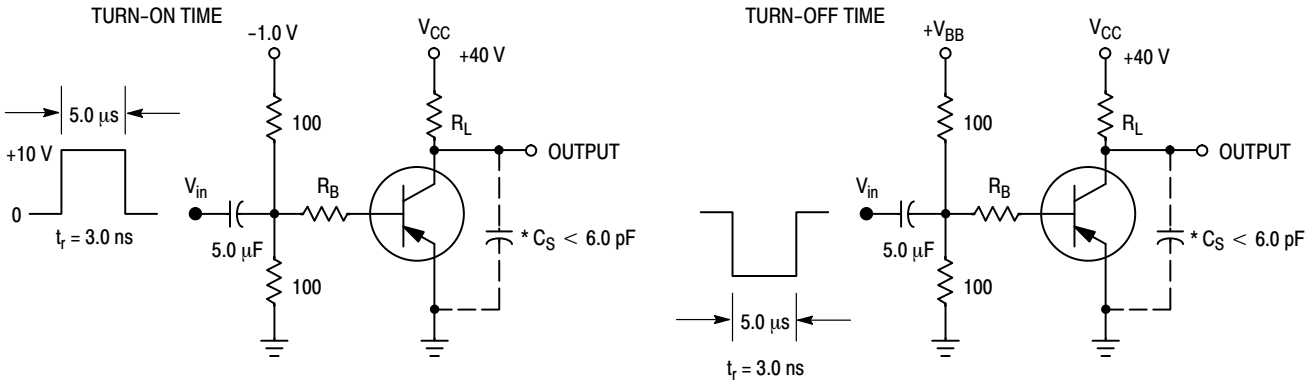
See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector – Emitter Breakdown Voltage (Note 3) (I_C = −1.0 mAdc, I_B = 0) MMBTA55 MMBTA56, SMMBTA56	$V_{(BR)CEO}$	 −60 −80	 – –	Vdc
Emitter – Base Breakdown Voltage (I_E = −100 μAdc, I_C = 0)	$V_{(BR)EBO}$	 −4.0	 –	Vdc
Collector Cutoff Current (V_{CE} = −60 Vdc, I_B = 0)	I_{CES}	 –	 −0.1	μAdc
Collector Cutoff Current (V_{CB} = −60 Vdc, I_E = 0) MMBTA55 (V_{CB} = −80 Vdc, I_E = 0) MMBTA56, SMMBTA56	I_{CBO}	 – –	 −0.1 −0.1	μAdc
ON CHARACTERISTICS				
DC Current Gain (I_C = −10 mAdc, V_{CE} = −1.0 Vdc) (I_C = −100 mAdc, V_{CE} = −1.0 Vdc)	h_{FE}	 100 100	 – –	–
Collector – Emitter Saturation Voltage (I_C = −100 mAdc, I_B = −10 mAdc)	$V_{CE(sat)}$	 –	 −0.25	Vdc
Base – Emitter On Voltage (I_C = −100 mAdc, V_{CE} = −1.0 Vdc)	$V_{BE(on)}$	 –	 −1.2	Vdc
SMALL– SIGNAL CHARACTERISTICS				
Current – Gain – Bandwidth Product (Note 4) (I_C = −100 mAdc, V_{CE} = −1.0 Vdc, f = 100 MHz)	f_T	 50	 –	MHz

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
4. f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.



*Total Shunt Capacitance of Test Jig and Connectors For PNP Test Circuits, Reverse All Voltage Polarities

Figure 1. Switching Time Test Circuits

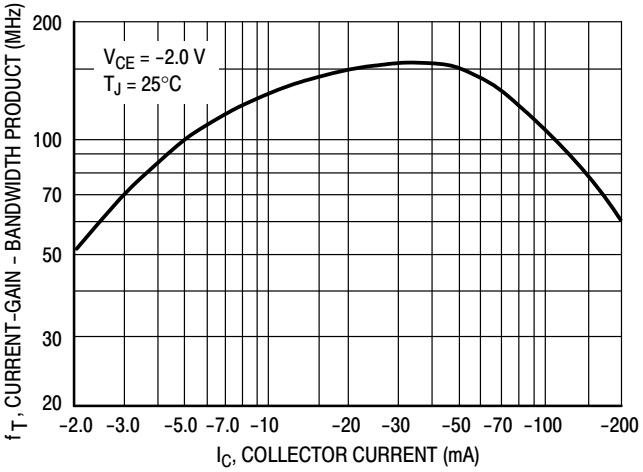


Figure 2. Current−Gain — Bandwidth Product

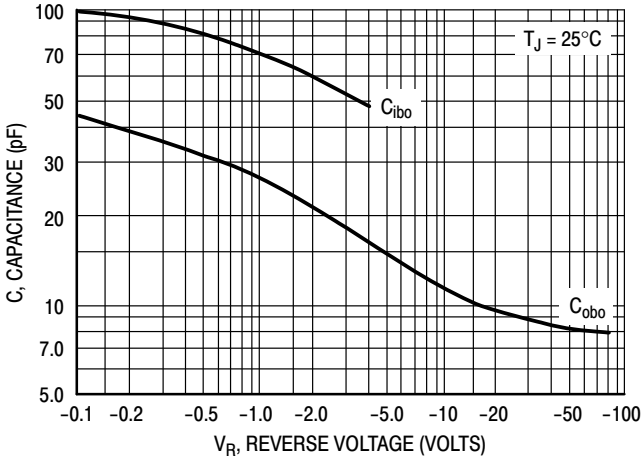


Figure 3. Capacitance

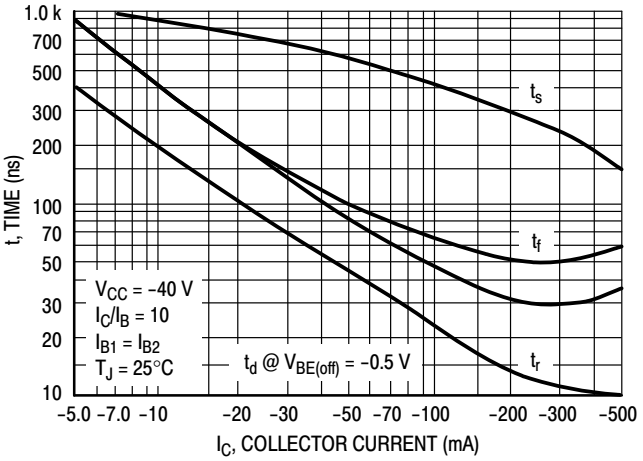


Figure 4. Switching Time

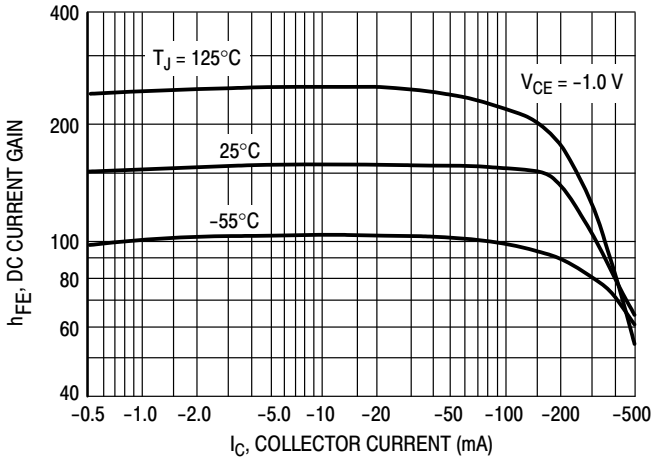


Figure 5. DC Current Gain

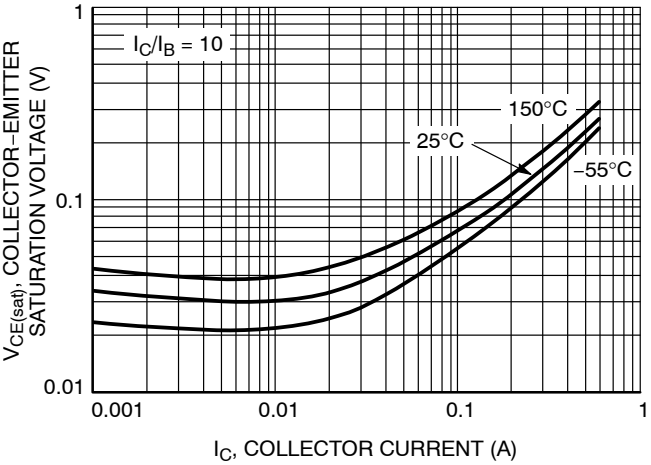


Figure 6. Collector Emitter Saturation Voltage vs. Collector Current

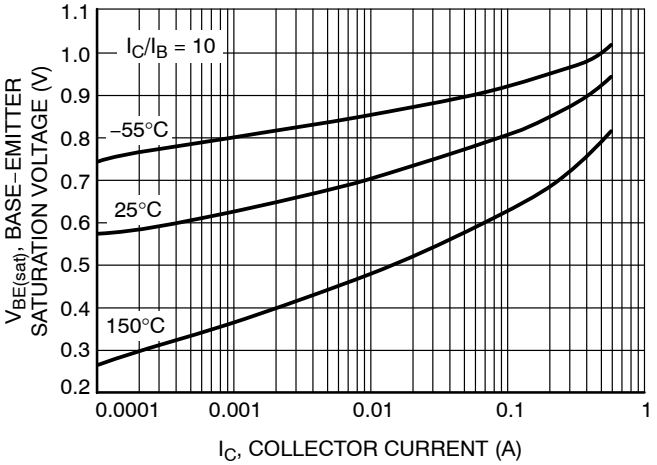


Figure 7. Base Emitter Saturation Voltage vs. Collector Current

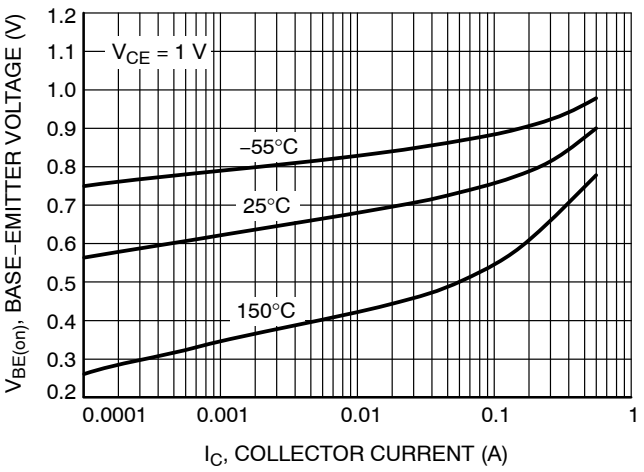


Figure 8. Base Emitter Voltage vs. Collector Current

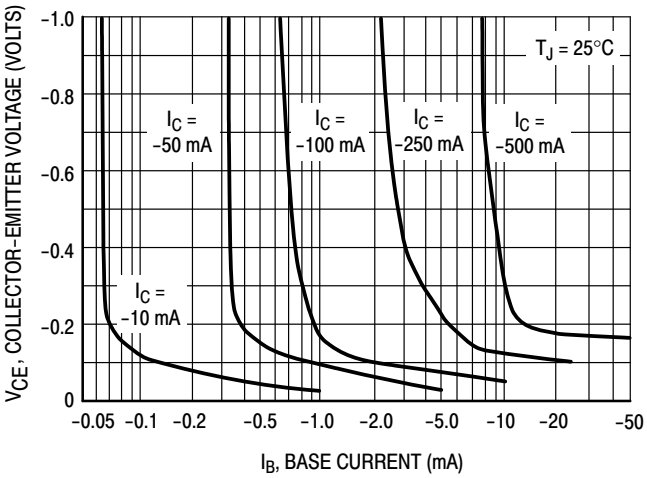


Figure 9. Collector Saturation Region

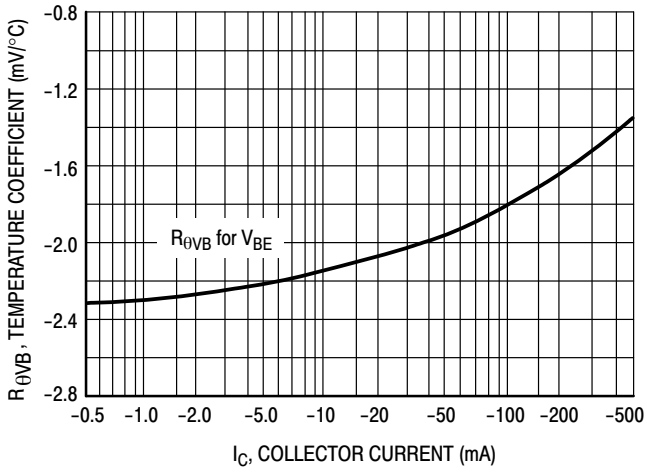


Figure 10. Base−Emitter Temperature Coefficient

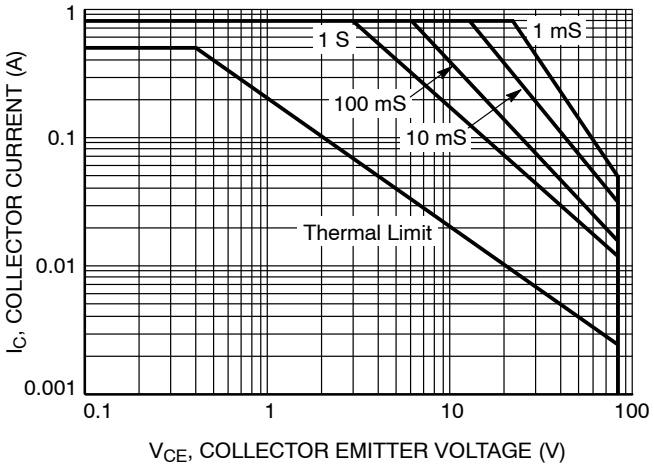


Figure 11. Safe Operating Area

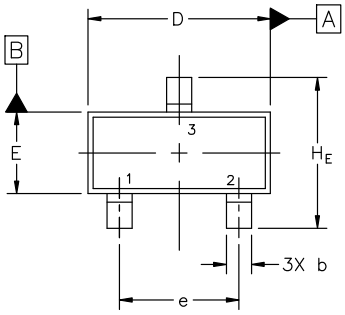
ORDERING INFORMATION

Device Order Number	Package Type	Shipping†
MMBTA55LT1G	SOT−23 (Pb−Free)	3,000 / Tape & Reel
MMBTA55LT3G	SOT−23 (Pb−Free)	10,000 / Tape & Reel
MMBTA56LT1G	SOT−23 (Pb−Free)	3,000 / Tape & Reel
SMMBTA56LT1G	SOT−23 (Pb−Free)	3,000 / Tape & Reel
MMBTA56LT3G	SOT−23 (Pb−Free)	10,000 / Tape & Reel
SMMBTA56LT3G	SOT−23 (Pb−Free)	10,000 / Tape & Reel

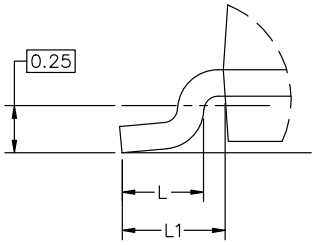
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

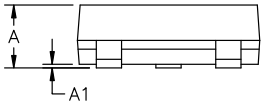
SOT−23 (TO−236) 2.90x1.30x1.00 1.90P
CASE 318
ISSUE AU



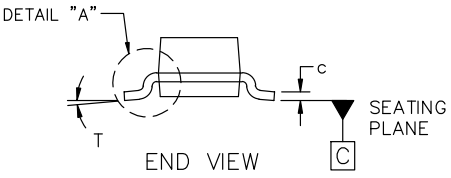
TOP VIEW



DETAIL "A"
Scale 3:1



SIDE VIEW

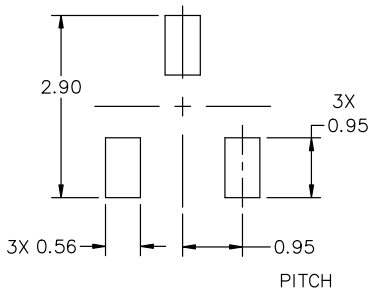


END VIEW

MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.89	1.00	1.11
A1	0.01	0.06	0.10
b	0.37	0.44	0.50
c	0.08	0.14	0.20
D	2.80	2.90	3.04
E	1.20	1.30	1.40
e	1.78	1.90	2.04
L	0.30	0.43	0.55
L1	0.35	0.54	0.69
H_E	2.10	2.40	2.64
T	0°	−−−	10°

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSIONS: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR



RECOMMENDED
MOUNTING FOOTPRINT

* For additional information on our Pb−Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
Technical Library: www.onsemi.com/design/resources/technical−documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support
For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales

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